

Abstract of the Disclosure

An integrated circuit including a composite polymer dielectric layer formed on a substrate is disclosed, wherein the composite polymer dielectric layer includes a first silane-containing layer formed on the substrate, wherein the first silane-containing layer is formed at least partially from an organosilane material, a polymer dielectric layer formed on the first silane-containing layer, and a second silane-containing layer formed on the polymer dielectric layer. In some embodiments, the first silane-containing layer and second silane-containing layer may be formed from organosilane materials having at least one unsaturated bond capable of free radical polymerization. Systems and methods for making the disclosed integrated circuits are also provided.